

Full Marks: 80

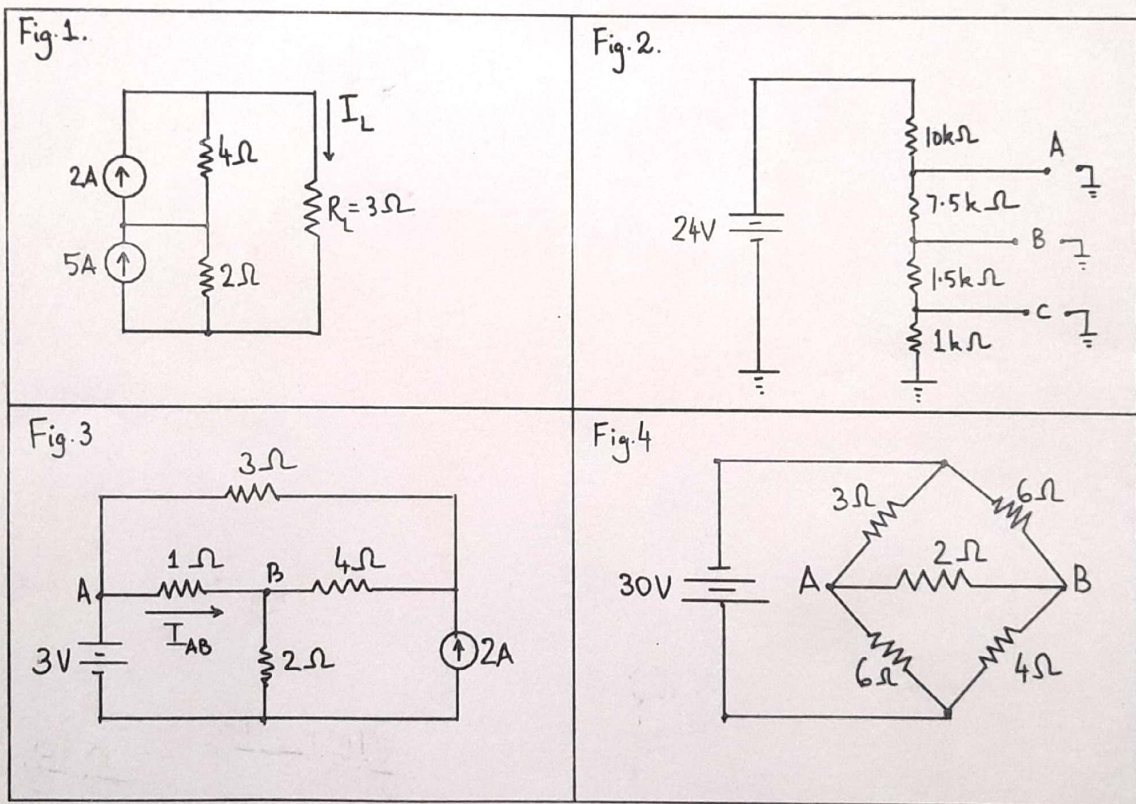
Date: 08/10/2024

Time: 9:30 PM - 11:30 AM

Instructions:

1. Attempt **ALL** the questions. Each question carries equal marks.
2. Answer each question sequentially beginning on a new page.
3. Use of a scientific calculator is permitted.

Q1. In the circuit shown in Fig.1, convert current sources to voltage sources and calculate the current I_L through the resistor $R_L = 3\Omega$.



- Q2.** Fig. 2 shows a voltage divider circuit. Determine the voltage that can be measured at terminals A, B, and C with respect to the ground.
- Q3.** Use superposition theorem to determine current I_{AB} indicated in the circuit shown in Fig. 3.
- Q4.** Apply Thevenin's theorem across the terminals A and B in the circuit shown in Fig. 4. Draw the Thevenin equivalent circuit mentioning the value of Thevenin voltage and resistance.

- Q5.** An intrinsic Germanium rod has the following dimensions: length = 1cm; width = 1mm; and thickness = 1mm. At temperature $T = 300\text{K}$, the intrinsic carrier density in Germanium is $2.5 \times 10^{13} \text{ cm}^{-3}$, the mobility of electrons is $\mu_e = 3900 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$ whereas the mobility of holes is $\mu_h = 1900 \text{ cm}^2\text{V}^{-1}\text{s}^{-1}$. Determine (i) electrical conductivity, (ii) electrical resistivity, and (iii) electrical resistance of the given rod.
- Q6.** Determine built-in potential of the p - n homojunction formed in a Silicon sample by doping it with the acceptor atoms $N_A = 10^{15} \text{ cm}^{-3}$ and with the donor atoms $N_D = 10^{15} \text{ cm}^{-3}$ at $T = 300\text{K}$. [Assume intrinsic carrier density at $T = 300\text{K}$ to be 10^{10} cm^{-3}]
- Q7.** Consider the circuit shown in Fig. 5. For the input voltage $v_{in}(t) = 15 \sin(314 t) \text{ V}$, and assuming the ideal diode model, plot the output waveform $v_{out}(t)$ indicating the values of maximum and minimum voltage.
- Q8.** Draw the waveform observed at terminals A, B, and C indicated in Fig. 6.

